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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	36MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	80
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	48K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f101vdt6

2.3.11 Power supply schemes

- V_{DD} = 2.0 to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 2.0 to 3.6 V: external analog power supplies for ADC, DAC, Reset blocks, RCs and PLL (minimum voltage to be applied to V_{DDA} is 2.4 V when the ADC or DAC is used). V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS}, respectively.
- V_{BAT} = 1.8 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

For more details on how to connect power pins, refer to *Figure 9: Power supply scheme*.

2.3.12 Power supply supervisor

The device has an integrated power-on reset (POR)/power-down reset (PDR) circuitry. It is always active, and ensures proper operation starting from/down to 2 V. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$, without the need for an external reset circuit.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software. Refer to *Table 12: Embedded reset and power control block characteristics* for the values of $V_{POR/PDR}$ and V_{PVD}.

2.3.13 Voltage regulator

The regulator has three operation modes: main (MR), low power (LPR) and power down.

- MR is used in the nominal regulation mode (Run)
- LPR is used in the Stop modes.
- Power down is used in Standby mode: the regulator output is in high impedance: the kernel circuitry is powered down, inducing zero consumption (but the contents of the registers and SRAM are lost)

This regulator is always enabled after reset. It is disabled in Standby mode.

2.3.14 Low-power modes

The STM32F101xC, STM32F101xD and STM32F101xE access line supports three low-power modes to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

- **Sleep** mode

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Stop** mode

  Stop mode achieves the lowest power consumption while retaining the content of SRAM and registers. All clocks in the 1.8 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- A 24-bit down counter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0.
- Programmable clock source

2.3.18 I²C bus

Up to two I²C bus interfaces can operate in multi-master and slave modes. They support standard and fast modes.
They support 7/10-bit addressing mode and 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is embedded.
They can be served by DMA and they support SMBus 2.0/PMBus.

2.3.19 Universal synchronous/asynchronous receiver transmitters (USARTs)

The STM32F101xC, STM32F101xD and STM32F101xE access line embeds three universal synchronous/asynchronous receiver transmitters (USART1, USART2 and USART3) and two universal asynchronous receiver transmitters (UART4 and UART5).

These five interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability. The five interfaces are able to communicate at speeds of up to 2.25 Mbit/s.

USART1, USART2 and USART3 also provide hardware management of the CTS and RTS signals, Smart Card mode (ISO 7816 compliant) and SPI-like communication capability. All interfaces can be served by the DMA controller except for UART5.

2.3.20 Serial peripheral interface (SPI)

Up to three SPIs are able to communicate up to 18 Mbits/s in slave and master modes in full-duplex and simplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

All SPIs can be served by the DMA controller.

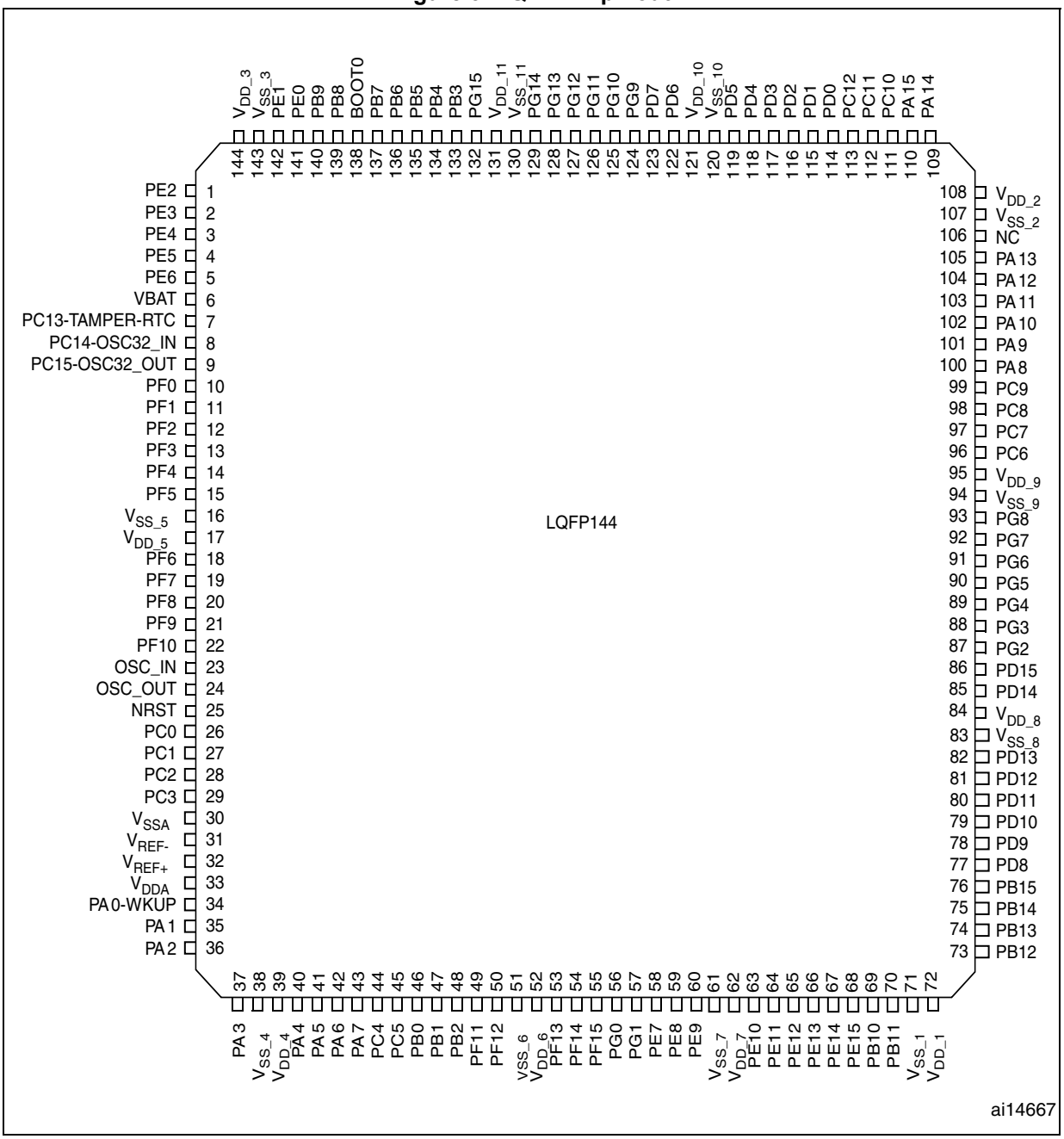
2.3.21 GPIOs (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high current-capable.

The I/Os alternate function configuration can be locked if needed following a specific sequence in order to avoid spurious writing to the I/Os registers.

3 Pinouts and pin descriptions

Figure 3. LQFP144 pinout



1. The above figure shows the package top view.

Table 5. STM32F101xC/STM32F101xD/STM32F101xE pin definitions (continued)

Pins			Pin name	Type(1)	I / O Level(2)	Main function(3) (after reset)	Alternate functions(4)	
LQFP144	LQFP64	LQFP100					Default	Remap
12	-	-	PF2	I/O	FT	PF2	FSMC_A2	-
13	-	-	PF3	I/O	FT	PF3	FSMC_A3	-
14	-	-	PF4	I/O	FT	PF4	FSMC_A4	-
15	-	-	PF5	I/O	FT	PF5	FSMC_A5	-
16	-	10	V_{SS_5}	S	-	V_{SS_5}	-	-
17	-	11	V_{DD_5}	S	-	V_{DD_5}	-	-
18	-	-	PF6	I/O	-	PF6	FSMC_NIORD	-
19	-	-	PF7	I/O	-	PF7	FSMC_NREG	-
20	-	-	PF8	I/O	-	PF8	FSMC_NIOWR	-
21	-	-	PF9	I/O	-	PF9	FSMC_CD	-
22	-	-	PF10	I/O	-	PF10	FSMC_INTR	-
23	5	12	OSC_IN	I	-	OSC_IN	-	PD0(7)
24	6	13	OSC_OUT	O	-	OSC_OUT	-	PD1(7)
25	7	14	NRST	I/O	-	NRST	-	-
26	8	15	PC0	I/O	-	PC0	ADC_IN10	-
27	9	16	PC1	I/O	-	PC1	ADC_IN11	-
28	10	17	PC2	I/O	-	PC2	ADC_IN12	-
29	11	18	PC3	I/O	-	PC3	ADC_IN13	-
30	12	19	V_{SSA}	S	-	V_{SSA}	-	-
31	-	20	V_{REF-}	S	-	V_{REF-}	-	-
32	-	21	V_{REF+}	S	-	V_{REF+}	-	-
33	13	22	V_{DDA}	S	-	V_{DDA}	-	-
34	14	23	PA0-WKUP	I/O	-	PA0	WKUP/ USART2_CTS(8)/ ADC_IN0/TIM5_CH1/ TIM2_CH1_ETR(8)	-
35	15	24	PA1	I/O	-	PA1	USART2_RTS(8)/ ADC_IN1/TIM5_CH2 TIM2_CH2(8)	-
36	16	25	PA2	I/O	-	PA2	USART2_TX(8)/ TIM5_CH3/ADC_IN2/ TIM2_CH3(8)	-

Table 5. STM32F101xC/STM32F101xD/STM32F101xE pin definitions (continued)

Pins			Pin name	Type(1)	I / O Level(2)	Main function(3) (after reset)	Alternate functions(4)	
LQFP144	LQFP64	LQFP100					Default	Remap
88	-	-	PG3	I/O	FT	PG3	FSMC_A13	-
89	-	-	PG4	I/O	FT	PG4	FSMC_A14	-
90	-	-	PG5	I/O	FT	PG5	FSMC_A15	-
91	-	-	PG6	I/O	FT	PG6	FSMC_INT2	-
92	-	-	PG7	I/O	FT	PG7	FSMC_INT3	-
93	-	-	PG8	I/O	FT	PG8	-	-
94	-	-	V_{SS_9}	S	-	V_{SS_9}	-	-
95	-	-	V_{DD_9}	S	-	V_{DD_9}	-	-
96	37	63	PC6	I/O	FT	PC6	-	TIM3_CH1
97	38	64	PC7	I/O	FT	PC7	-	TIM3_CH2
98	39	65	PC8	I/O	FT	PC8	-	TIM3_CH3
99	40	66	PC9	I/O	FT	PC9	-	TIM3_CH4
100	41	67	PA8	I/O	FT	PA8	USART1_CK/ MCO	-
101	42	68	PA9	I/O	FT	PA9	USART1_TX(8)	-
102	43	69	PA10	I/O	FT	PA10	USART1_RX(8)	-
103	44	70	PA11	I/O	FT	PA11	USART1_CTS	-
104	45	71	PA12	I/O	FT	PA12	USART1_RTS	-
105	46	72	PA13	I/O	FT	JTMS-SWDIO	-	PA13
106	-	73	Not connected					
107	47	74	V_{SS_2}	S	-	V_{SS_2}	-	-
108	48	75	V_{DD_2}	S	-	V_{DD_2}	-	-
109	49	76	PA14	I/O	FT	JTCK-SWCLK	-	PA14
110	50	77	PA15	I/O	FT	JTDI	SPI3_NSS	TIM2_CH1_ETR/ PA15 /SPI1_NSS
111	51	78	PC10	I/O	FT	PC10	UART4_TX	USART3_TX
112	52	79	PC11	I/O	FT	PC11	UART4_RX	USART3_RX
113	53	80	PC12	I/O	FT	PC12	UART5_TX	USART3_CK
114	-	81	PD0	I/O	FT	OSC_IN(8)	FSMC_D2(9)	-
115	-	82	PD1	I/O	FT	OSC_OUT(8)	FSMC_D3(9)	-

Table 8. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD}	Total current into V_{DD}/V_{DDA} power lines (source)(1)	150	mA
ΣI_{VSS}	Total current out of V_{SS} ground lines (sink)(1)	150	
I_{IO}	Output current sunk by any I/O and control pin	25	
	Output current source by any I/Os and control pin	– 25	
$I_{INJ(PIN)}$(2)	Injected current on five volt tolerant pins(3)	-5/+0	
	Injected current on any other pin(4)	± 5	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins)(5)	± 25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. Negative injection disturbs the analog performance of the device. See note 3 below *Table 58 on page 98*.
3. Positive injection is not possible on these I/Os. A negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 7: Voltage characteristics* for the maximum allowed input voltage values.
4. A positive injection is induced by $V_{IN}>V_{DD}$ while a negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 7: Voltage characteristics* for the maximum allowed input voltage values.
5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 9. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C

5.3.4 Embedded reference voltage

The parameters given in *Table 13* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 10*.

Table 13. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	–40 °C < T_A < +85 °C	1.16	1.20	1.24	V
$T_{S\_vrefint}$(1)	ADC sampling time when reading the internal reference voltage	-	-	5.1	17.1(2)	µs
V_{RERINT}(2)	Internal reference voltage spread over the temperature range	V_{DD} = 3 V ±10 mV	-	-	10	mV
T_{Coeff}(2)	Temperature coefficient	-	-	-	100	ppm/ °C

1. Shortest sampling time can be determined in the application by multiple iterations.
2. Guaranteed by design, not tested in production.

5.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.
The current consumption is measured as described in *Figure 10: Current consumption measurement scheme*.
All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to Dhrystone 2.1 code.

Maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except if it is explicitly mentioned
- The Flash access time is adjusted to f_{HCLK} frequency (0 wait state from 0 to 24 MHz, 1 wait state from 24 to 36 MHz)
- Prefetch in on (reminder: this bit must be set before clock setting and bus prescaling)
- When the peripherals are enabled $f_{PCLK1} = f_{HCLK/2}$, $f_{PCLK2} = f_{HCLK}$

The parameters given in *Table 14* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 10*.

Figure 11. Typical current consumption in Run mode versus frequency (at 3.6 V) - code with data processing running from RAM, peripherals enabled

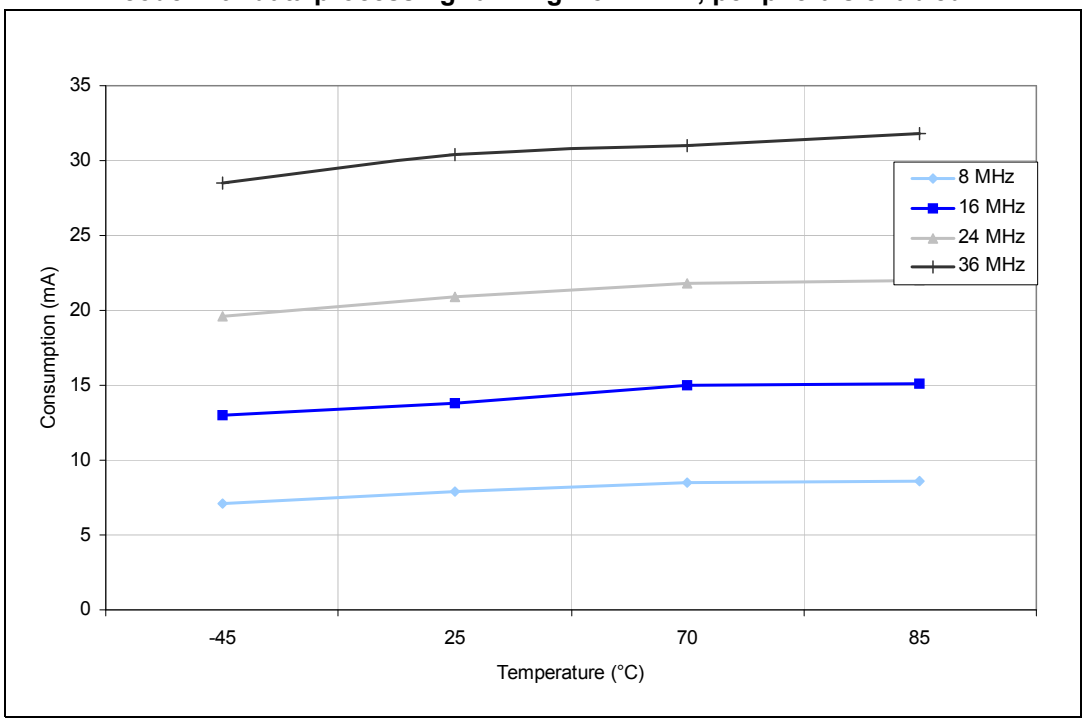


Figure 12. Typical current consumption in Run mode versus frequency (at 3.6 V) - code with data processing running from RAM, peripherals disabled

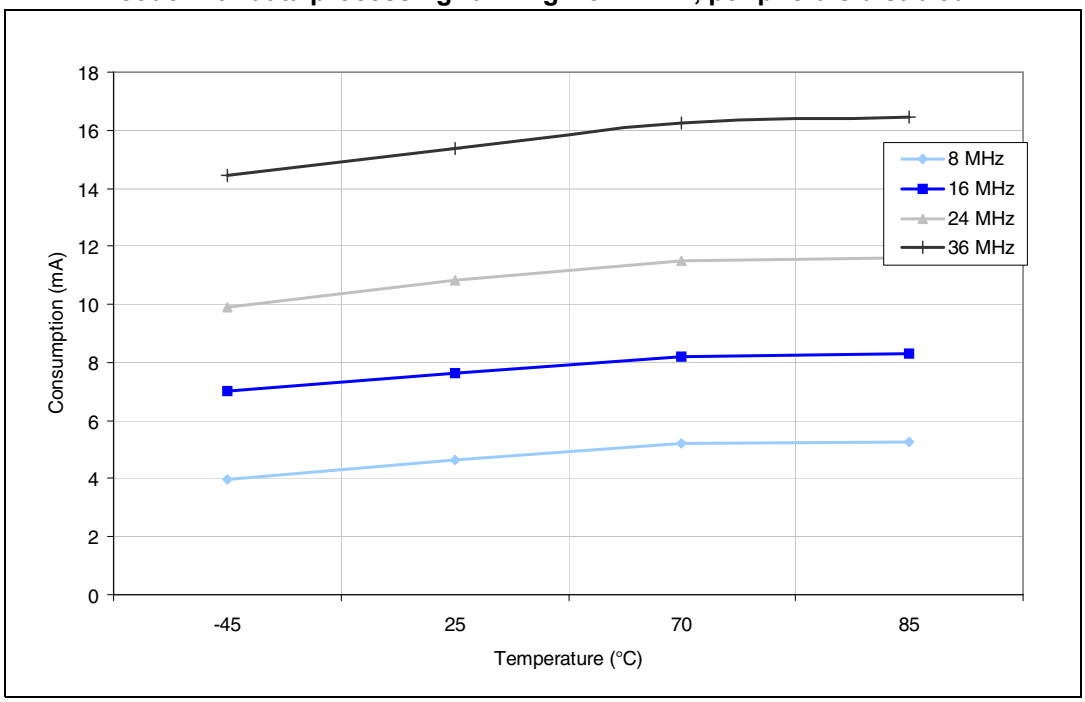


Figure 13. Typical current consumption on V_{BAT} with RTC on vs. temperature at different V_{BAT} values

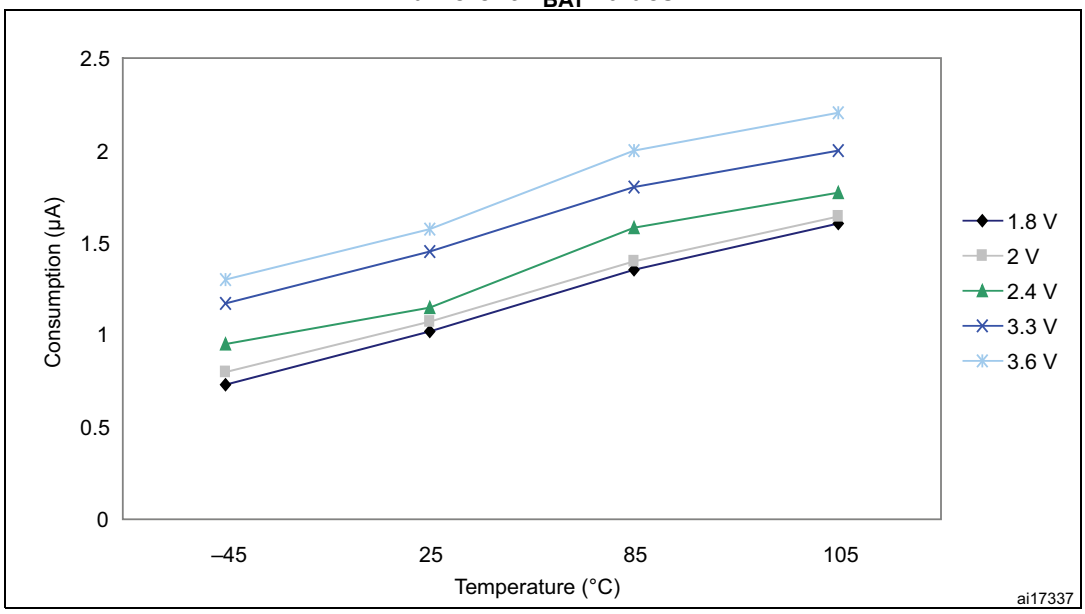


Figure 14. Typical current consumption in Stop mode with regulator in run mode versus temperature at different V_{DD} values

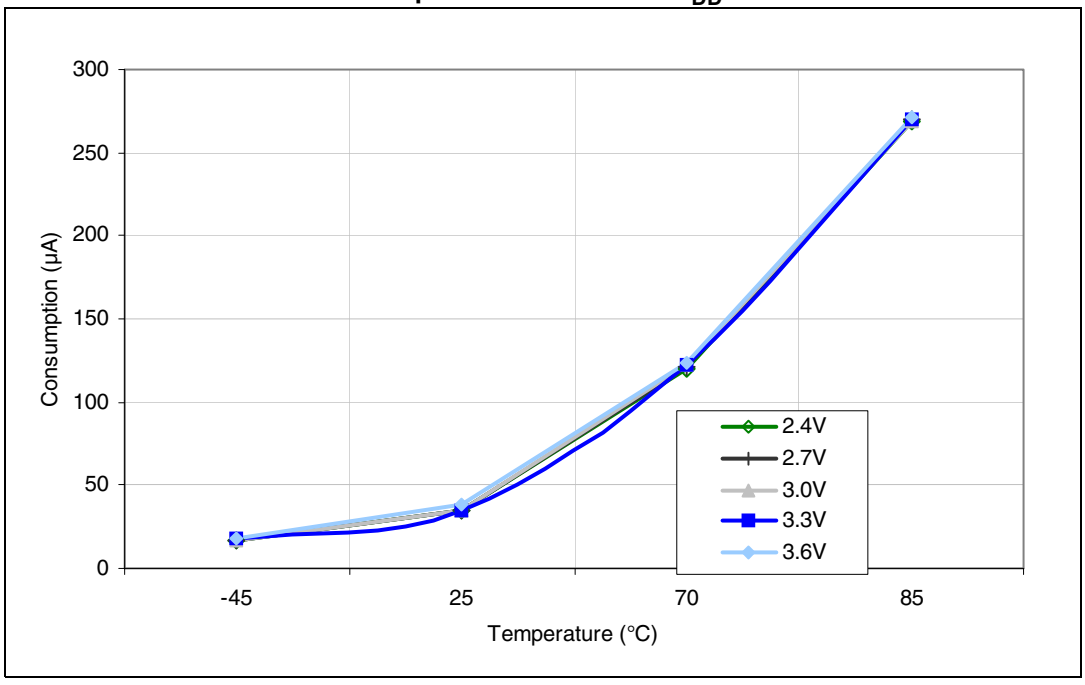


Table 19. Typical current consumption in Sleep mode, code running from Flash or RAM

Symbol	Parameter	Conditions	f_{HCLK}	Typ(1)	Typ(1)	Unit
				All peripherals enabled(2)	All peripherals disabled	
I_{DD}	Supply current in Sleep mode	External clock(3)	36 MHz	15.1	3.6	mA
			24 MHz	10.4	2.6	
			16 MHz	7.2	2	
			8 MHz	3.9	1.3	
			4 MHz	2.6	1.2	
			2 MHz	1.85	1.15	
			1 MHz	1.5	1.1	
			500 kHz	1.3	1.05	
			125 kHz	1.2	1.05	
		Running on High Speed Internal RC (HSI), AHB prescaler used to reduce the frequency	36 MHz	14.5	3	
			24 MHz	9.8	2	
			16 MHz	6.6	1.4	
			8 MHz	3.3	0.7	
			4 MHz	2	0.6	
			2 MHz	1.25	0.55	
			1 MHz	0.9	0.5	
			500 kHz	0.7	0.45	
			125 kHz	0.6	0.45	

1. Typical values are measures at T_A = 25 °C, V_{DD} = 3.3 V.
2. Add an additional power consumption of 0.8 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is on (ADON bit is set in the ADC_CR2 register).
3. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in *Table 20*. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on
- ambient operating temperature and V_{DD} supply voltage conditions summarized in *Table 7*.

Table 33. Asynchronous multiplexed NOR/PSRAM read timings(1)(2) (continued)

Symbol	Parameter	Min	Max	Unit
$t_{h(A\_NOE)}$	Address hold time after FSMC_NOE high	t_{HCLK}	-	ns
$t_{h(BL\_NOE)}$	FSMC_BL hold time after FSMC_NOE high	0	-	ns
$t_{v(BL\_NE)}$	FSMC_NEx low to FSMC_BL valid	-	0	ns
$t_{su(Data\_NE)}$	Data to FSMC_NEx high setup time	$2t_{HCLK}$ + 24	-	ns
$t_{su(Data\_NOE)}$	Data to FSMC_NOE high setup time	$2t_{HCLK}$ + 25	-	ns
$t_{h(Data\_NE)}$	Data hold time after FSMC_NEx high	0	-	ns
$t_{h(Data\_NOE)}$	Data hold time after FSMC_NOE high	0	-	ns

1. C_L = 15 pF.
2. Guaranteed by characterization results, not tested in production.

2. Guaranteed by characterization results, not tested in production.

Figure 28. Synchronous non-multiplexed PSRAM write timings

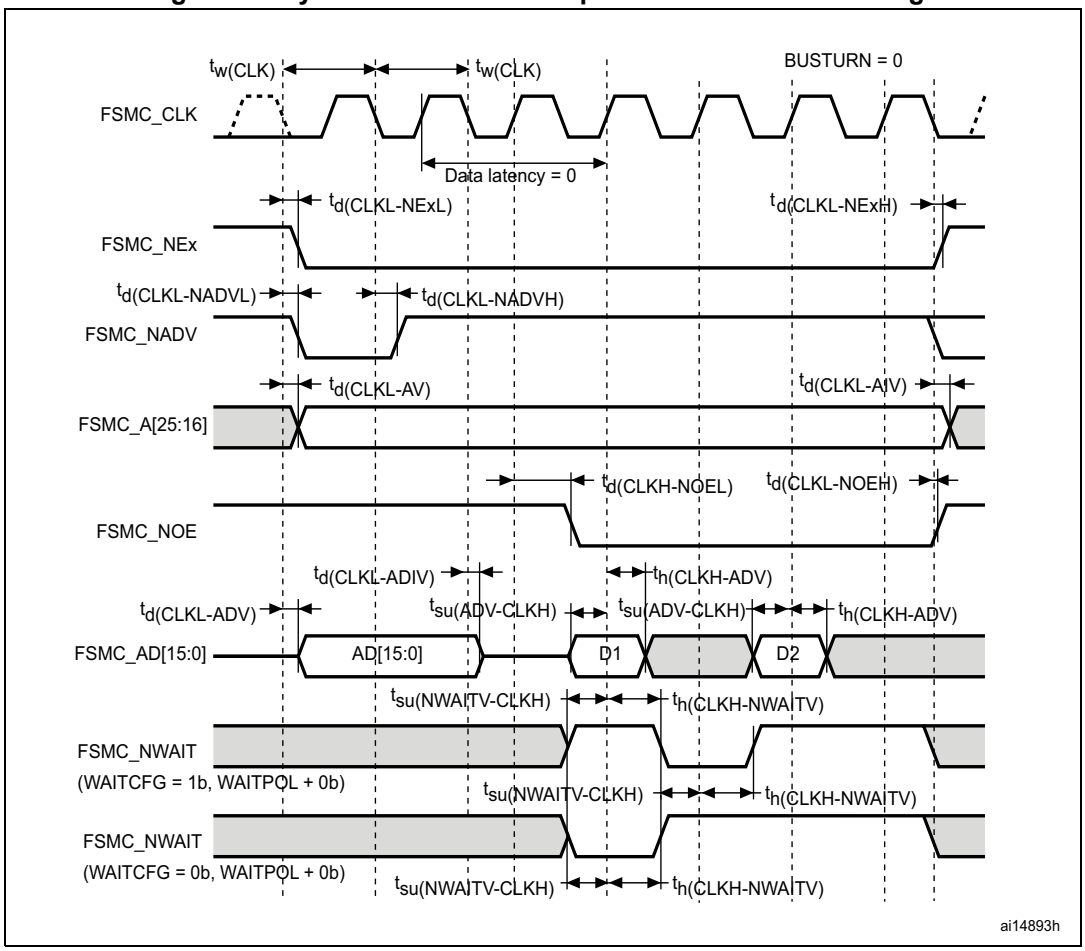


Table 38. Synchronous non-multiplexed PSRAM write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FSMC_CLK period	55.5	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low (x = 0...2)	-	2	ns
$t_{d(CLKL-NExH)}$	FSMC_CLK low to FSMC_NEx high (x = 0...2)	2	-	ns
$t_{d(CLKL-NADVL)}$	FSMC_CLK low to FSMC_NADV low	-	4	ns
$t_{d(CLKL-NADVH)}$	FSMC_CLK low to FSMC_NADV high	5	-	ns
$t_{d(CLKL-AV)}$	FSMC_CLK low to FSMC_Ax valid (x = 16...25)	-	0	ns
$t_{d(CLKL-AIV)}$	FSMC_CLK low to FSMC_Ax invalid (x = 16...25)	2	-	ns
$t_{d(CLKL-NWEL)}$	FSMC_CLK low to FSMC_NWE low	-	1	ns
$t_{d(CLKL-NWEH)}$	FSMC_CLK low to FSMC_NWE high	1	-	ns
$t_{d(CLKL-Data)}$	FSMC_D[15:0] valid data after FSMC_CLK low	-	6	ns
$t_{su(NWAITV-CLKH)}$	FSMC_NWAIT valid before FSMC_CLK high	7	-	ns

Figure 34. PC Card/CompactFlash controller waveforms for I/O space write access

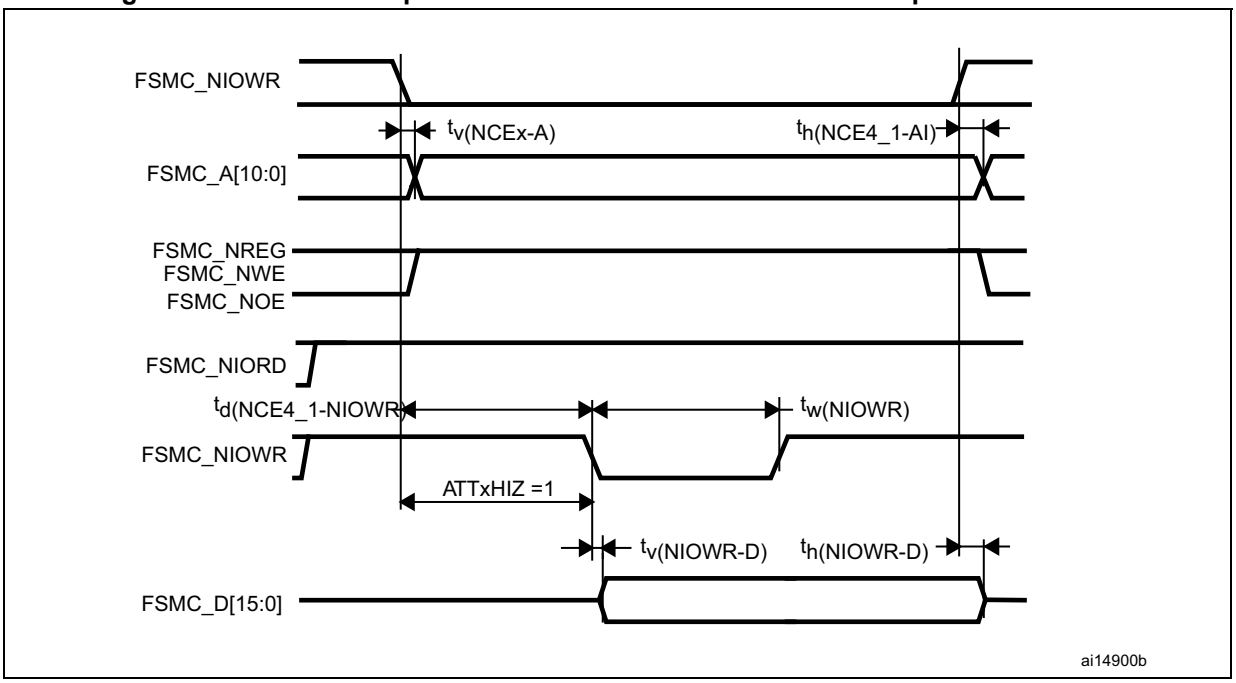


Table 39. Switching characteristics for PC Card/CF read and write cycles(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{v(NCEx-A)}$ $t_{v(NCE4\_1-A)}$	FSMC_NCEx low (x = 4_1/4_2) to FSMC_Ay valid (y = 0...10) FSMC_NCE4_1 low (x = 4_1/4_2) to FSMC_Ay valid (y = 0...10)	-	0	ns
$t_{h(NCEx-AI)}$ $t_{h(NCE4\_1-AI)}$	FSMC_NCEx high (x = 4_1/4_2) to FSMC_Ax invalid (x = 0...10) FSMC_NCE4_1 high (x = 4_1/4_2) to FSMC_Ax invalid (x = 0...10)	2.5	-	ns
$t_{d(NREG-NCEx)}$ $t_{d(NREG-NCE4\_1)}$	FSMC_NCEx low to FSMC_NREG valid FSMC_NCE4_1 low to FSMC_NREG valid	-	5	ns
$t_{h(NCEx-NREG)}$ $t_{h(NCE4\_1-NREG)}$	FSMC_NCEx high to FSMC_NREG invalid FSMC_NCE4_1 high to FSMC_NREG invalid	t_{HCLK} + 3	-	ns
$t_{d(NCE4\_1-NOE)}$	FSMC_NCE4_1 low to FSMC_NOE low	-	$5t_{HCLK}$ + 2	ns
$t_{w(NOE)}$	FSMC_NOE low width	$8t_{HCLK}$ –1.5	$8t_{HCLK}$ + 1	ns
$t_{d(NOE-NCE4\_1}$	FSMC_NOE high to FSMC_NCE4_1 high	$5t_{HCLK}$ + 2	-	ns
$t_{su(D-NOE)}$	FSMC_D[15:0] valid data before FSMC_NOE high	25	-	ns
$t_{h(NOE-D)}$	FSMC_D[15:0] valid data after FSMC_NOE high	15	-	ns
$t_{w(NWE)}$	FSMC_NWE low width	$8t_{HCLK}$ – 1	$8t_{HCLK}$ + 2	ns
$t_{d(NWE-NCE4\_1)}$	FSMC_NWE high to FSMC_NCE4_1 high	$5t_{HCLK}$ + 2	-	ns
$t_{d(NCE4\_1-NWE)}$	FSMC_NCE4_1 low to FSMC_NWE low	-	$5t_{HCLK}$ + 1.5	ns
$t_{v(NWE-D)}$	FSMC_NWE low to FSMC_D[15:0] valid	-	0	ns
$t_{h(NWE-D)}$	FSMC_NWE high to FSMC_D[15:0] invalid	$11t_{HCLK}$	-	ns

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 56. R_{AIN} max for f_{ADC} = 14 MHz(1)

T_s (cycles)	t_S (µs)	R_{AIN} max (kΩ)
1.5	0.11	0.4
7.5	0.54	5.9
13.5	0.96	11.4
28.5	2.04	25.2
41.5	2.96	37.2
55.5	3.96	50
71.5	5.11	NA
239.5	17.1	NA

1. Guaranteed by design, not tested in production.

Table 57. ADC accuracy - limited test conditions(1)(2)

Symbol	Parameter	Test conditions	Typ	Max(3)	Unit
ET	Total unadjusted error	f_{PCLK2} = 28 MHz, f_{ADC} = 14 MHz, R_{AIN} < 10 kΩ, V_{DDA} = 3 V to 3.6 V, T_A = 25 °C Measurements made after ADC calibration V_{REF+} = V_{DDA}	±1.3	±2	LSB
EO	Offset error		±1	±1.5	
EG	Gain error		±0.5	±1.5	
ED	Differential linearity error		±0.7	±1	
EL	Integral linearity error		±0.8	±1.5	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
   Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 5.3.13* does not affect the ADC accuracy.
3. Guaranteed by characterization results, not tested in production.

Table 58. ADC accuracy(1) (2)(3)

Symbol	Parameter	Test conditions	Typ	Max(4)	Unit
ET	Total unadjusted error	f_{PCLK2} = 28 MHz, f_{ADC} = 14 MHz, R_{AIN} < 10 kΩ, V_{DDA} = 2.4 V to 3.6 V Measurements made after ADC calibration	±2	±5	LSB
EO	Offset error		±1.5	±2.5	
EG	Gain error		±1.5	±3	
ED	Differential linearity error		±1	±2	
EL	Integral linearity error		±1.5	±3	

1. ADC DC accuracy values are measured after internal calibration.
2. Better performance could be achieved in restricted V_{DD}, frequency, V_{REF} and temperature ranges.
3. ADC accuracy vs. negative injection current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current.
   Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 5.3.13* does not affect the ADC accuracy.
4. Guaranteed by characterization results, not tested in production.

Figure 49. ADC accuracy characteristics

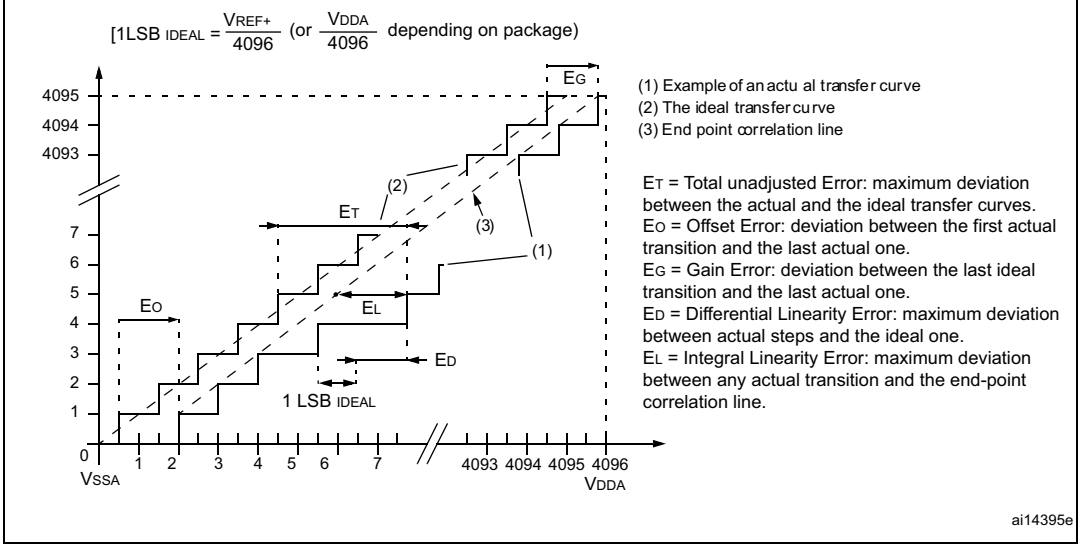
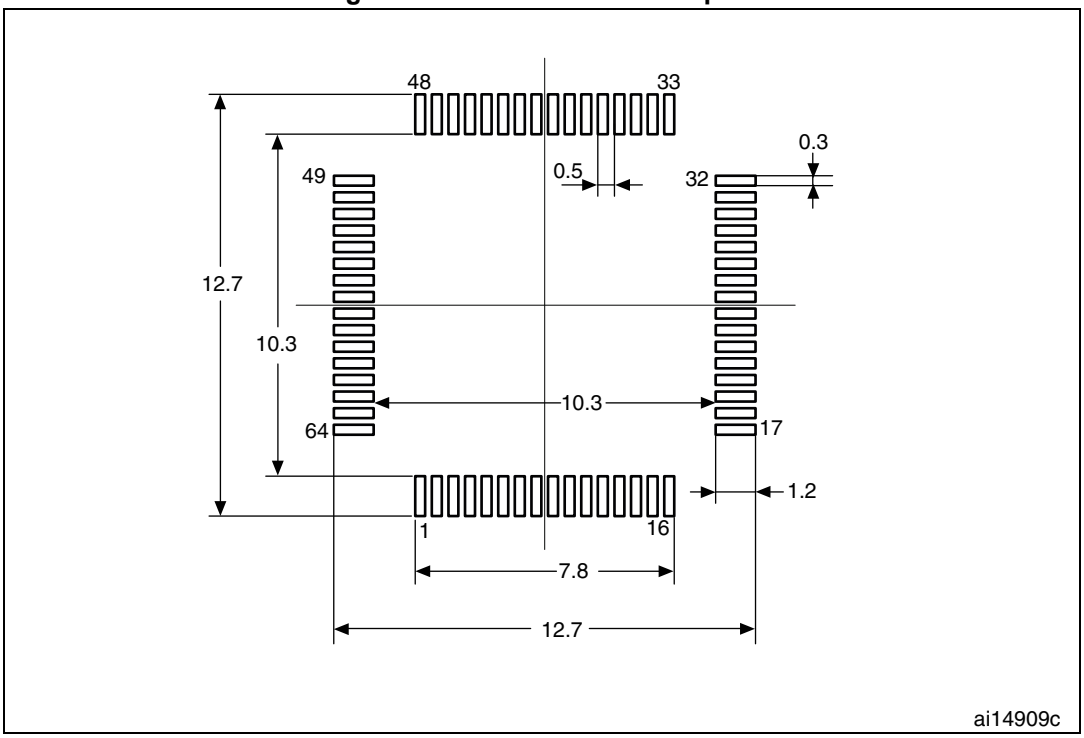


Table 63. LQFP64 – 10 x 10 mm, 64 pin low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
e	-	0.500	-	-	0.0197	-
θ	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 61. Recommended footprint



1. Dimensions are in millimeters.

6.4.2 Evaluating the maximum junction temperature for an application

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in *Table 65: Ordering information scheme*.

Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and, to a specific maximum junction temperature. Here, only temperature range 6 is available (–40 to 85 °C).

The following example shows how to calculate the temperature range needed for a given application, making it possible to check whether the required temperature range is compatible with the STM32F10xxx junction temperature range.

Example: High-performance application

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 82 °C (measured according to JESD51-2), I_{DDmax} = 50 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V and maximum 8 I/Os used at the same time in output mode at low level with I_{OL} = 20 mA, V_{OL}= 1.3 V

P_{INTmax} = 50 mA × 3.5 V= 175 mW

P_{IOmax} = 20 × 8 mA × 0.4 V + 8 × 20 mA × 1.3 V = 272 mW

This gives: P_{INTmax} = 175 mW and P_{IOmax} = 272 mW

P_{Dmax} = 175 + 272 = 447 mW

Thus: P_{Dmax} = 447 mW

Using the values obtained in *Table 65* T_{Jmax} is calculated as follows:

– For LQFP64, 45 °C/W

T_{Jmax} = 82 °C + (45 °C/W × 447 mW) = 82 °C + 20.1 °C = 102.1 °C

This is within the junction temperature range of the STM32F10xxx (–40 < T_J < 105 °C).

Figure 63. LQFP64 P_D max vs. T_A

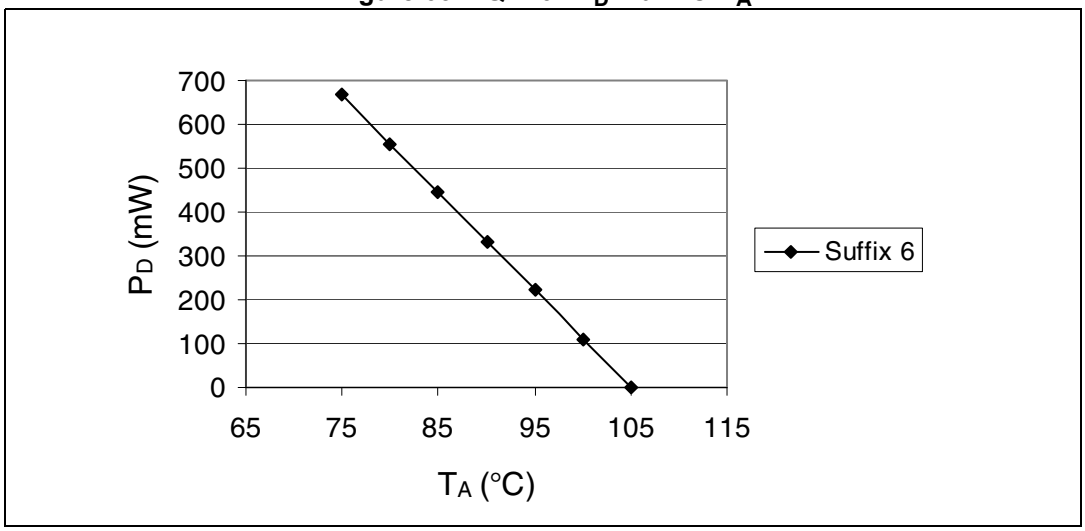


Table 66. Document revision history (continued)

Date	Revision	Changes
21-Jul-2008	3	Document status promoted from Preliminary Data to full datasheet. *FSMC (flexible static memory controller) on page 15* modified. *Power supply supervisor on page 17* modified and V_{DDA} added to *Table 10: General operating conditions on page 40*. Table notes revised in *Section 5: Electrical characteristics*. Capacitance modified in *Figure 9: Power supply scheme on page 37*. *Table 52: SCL frequency (f_{PCLK1}= 36 MHz, V_{DD} = V_{DD_I2C} = 3.3 V)* updated. *Table 54: SPI characteristics* modified, $t_{h(NSS)}$ modified in *Figure 46: SPI timing diagram - slave mode and CPHA=0 on page 94*. Minimum SDA and SCL fall time value for Fast mode removed from *Table 51: I^2C characteristics on page 90*, note 1 modified. I_{DD_VBAT} values added to *Table 17: Typical and maximum current consumptions in Stop and Standby modes on page 45*. *Table 30: Flash memory endurance and data retention on page 59* updated. f_{HCLK} corrected in *Table 41: EMS characteristics*. $t_{su(NSS)}$ modified in *Table 54: SPI characteristics*. EO corrected in *Table 58: ADC accuracy on page 98*, f_{PCLK2} corrected in *Table 57: ADC accuracy - limited test conditions* and *Table 58: ADC accuracy*. *Figure 50: Typical connection diagram using the ADC on page 99* and note below corrected. Typical T_{S_temp} value removed from *Table 60: TS characteristics on page 102*. *Section 6.1: LQFP144 package information on page 103* updated, Small text changes.
12-Dec-2008	4	*General-purpose timers (TIMx) on page 19* updated, *Table 3: STM32F101xx family* updated to show the low-density family, *Table 4: Timer feature comparison* added *Figure 1: STM32F101xC, STM32F101xD and STM32F101xE access line block diagram* updated. *Note 9* added, main function after reset and *Note 5* updated in *Table 5: STM32F101xC/STM32F101xD/STM32F101xE pin definitions*. *Note 2* modified below *Table 7: Voltage characteristics on page 38*, $\lvert\Delta V_{DDx}\rvert$ min and $\lvert\Delta V_{DDx}\rvert$ min removed. Measurement conditions specified in *Section 5.3.5: Supply current characteristics on page 42*. *General input/output characteristics on page 82* modified. Max values at T_A = 85 °C updated in *Table 17: Typical and maximum current consumptions in Stop and Standby modes on page 45*. *Section 5.3.10: FSMC characteristics on page 59* revised. Values added to *Table 42: EMI characteristics on page 80*. I_{VREF} added to *Table 55: ADC characteristics on page 96*. *Table 64: Package thermal characteristics on page 113* updated, Small text changes.

Table 66. Document revision history (continued)

Date	Revision	Changes
19-Apr-2011	8	Updated footnotes below *Table 7: Voltage characteristics on page 38* and *Table 8: Current characteristics on page 39* Updated tw min in *Table 21: High-speed external user clock characteristics on page 51* Updated startup time in *Table 24: LSE oscillator characteristics (f_{LSE} = 32.768 kHz) on page 55* Updated *Table 31: Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings on page 60* Updated FSMC sync data latency in *Figure 25* thru *Figure 28* Updated *Figure 38: NAND controller waveforms for common memory write access* and *Table 40: Switching characteristics for NAND Flash read and write cycles on page 78* Updated *Figure 44: Recommended NRST pin protection* Added *Section 5.3.13: I/O current injection characteristics* Updated *Section 5.3.13: I/O current injection characteristics* Updated note 2 in *Table 51: I^2C characteristics on page 90* Updated *Figure 45: I^2C bus AC waveforms and measurement circuit(1)*
15-May-2015	9	Added OSC_IN/OSC_OUT remap functions and updated PD0/PD1 in *Table 5: STM32F101xC/STM32F101xD/STM32F101xE pin definitions*. Modified *Section 2.3.21: GPIOs (general-purpose inputs/outputs) on page 20*. Updated notes related to parameters not tested in production in the whole document. Updated *Table 20: Peripheral current consumption on page 50*. Updated CDM standard and values in *Section : Electrostatic discharge (ESD)*. Modified *Section : Output driving current on page 84*. Updated *Figure 43: I/O AC characteristics definition*. Updated conditions related to *Section : I^2C interface characteristics*. Modified *Table 51: I^2C characteristics on page 90*, updated *Figure 45: I^2C bus AC waveforms and measurement circuit(1)* and V_{DD}/V_{DD_I2C} conditions in *Table 52: SCL frequency (f_{PCLK1}= 36 MHz, V_{DD} = V_{DD_I2C} = 3.3 V) on page 91*. Modified *Figure 48: SPI timing diagram - master mode(1) on page 95*. Modified note 3 in *Table 58: ADC accuracy on page 98*. Updated I_{DDA} definition in *Table 59: DAC characteristics on page 100* and removed comment related to the offset parameter for ±10 mV. Corrected “CLKL-NOEL” in *Section 5.3.10: FSMC characteristics on page 59*. *Updated Section 6.1: LQFP144 package information on page 103 and added Section : Device marking for LQFP144 on page 106.* *Updated Section 6.2: LQFP100 package information on page 107 and added Section : Device marking for LQFP100 on page 109.* *Updated Section 6.3: LQFP64 information on page 110 and added Section : Device marking for LQFP64 on page 112.*